

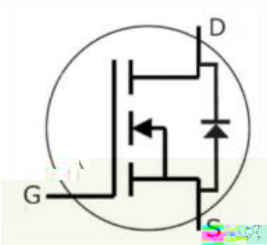
S3M010120V1K-A



TriQSiC™1200V Silicon Carbide Power MOSFET G3

Features

-
-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size	W x L	mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V _{DS}	I _{DS} ≤	R _{DS(on)} , typ	T _{J,max}

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Features	1
Benefits	

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1200V SiC Power MOSFET

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	

2 Electrical characteristics

Table 4 Static characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

Table 5 **Dynamic characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

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2.3 Switching characteristics

Table 6 Dynamic characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

Table 7 Body diode characteristics

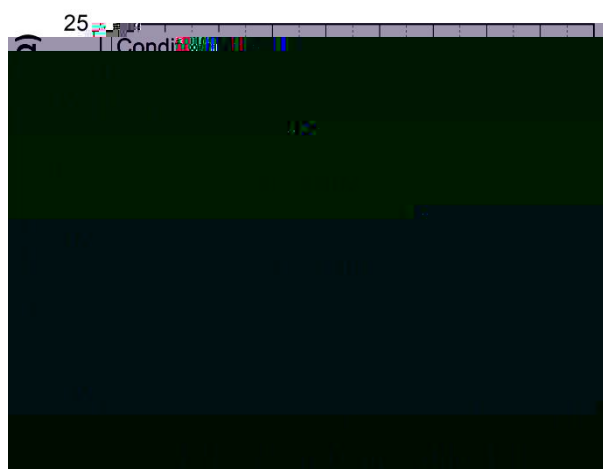
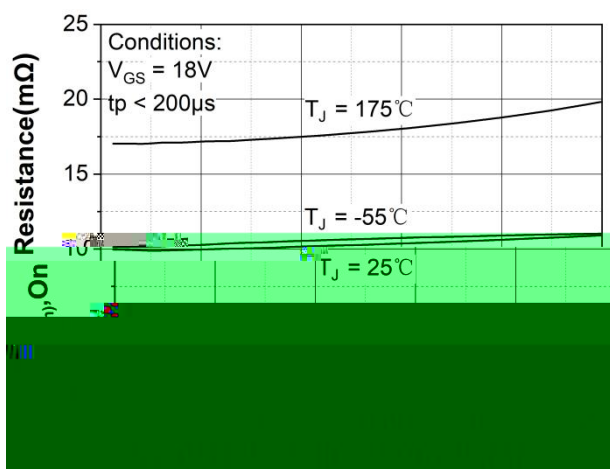
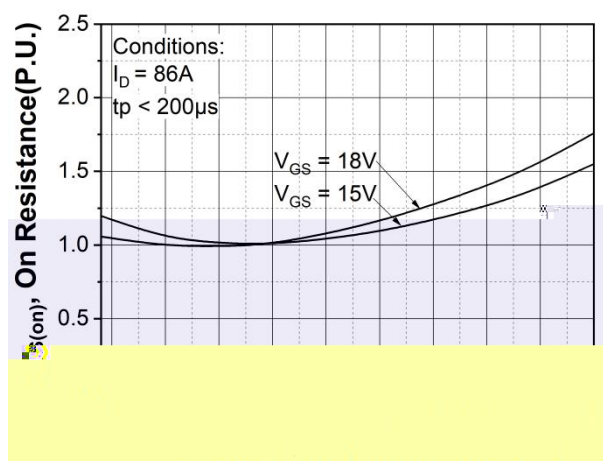
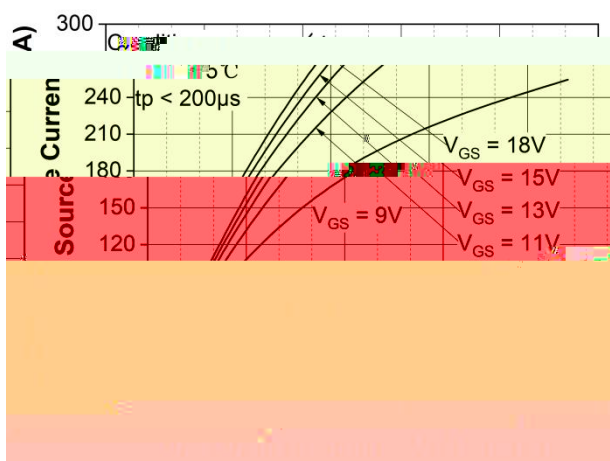
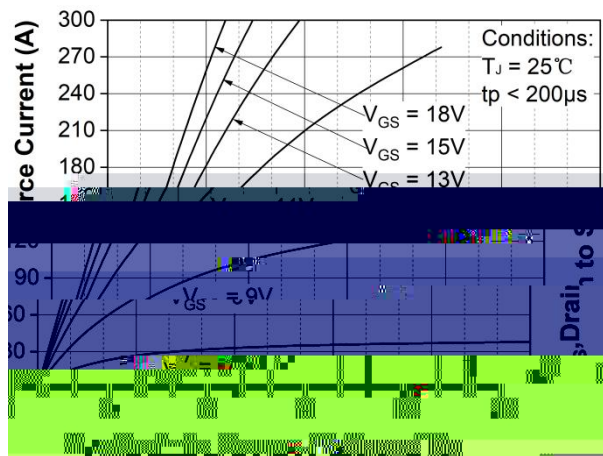
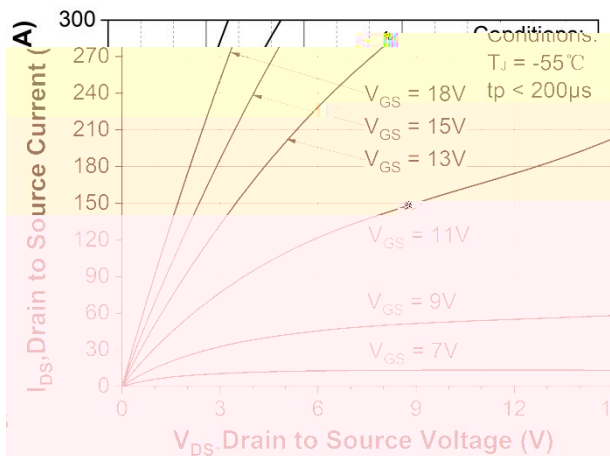
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

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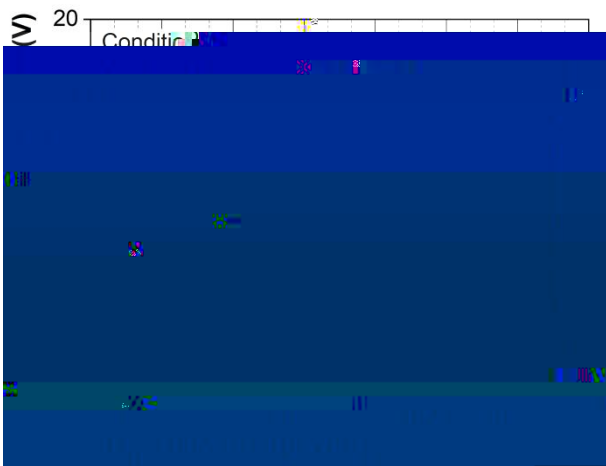
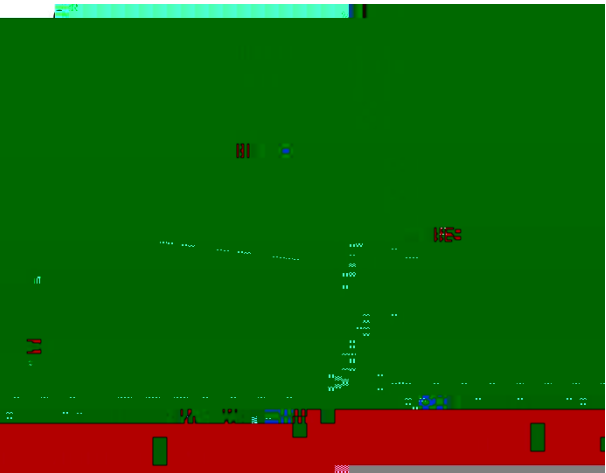
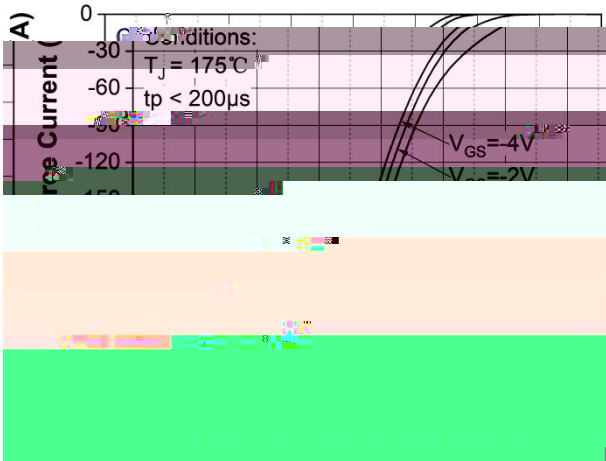
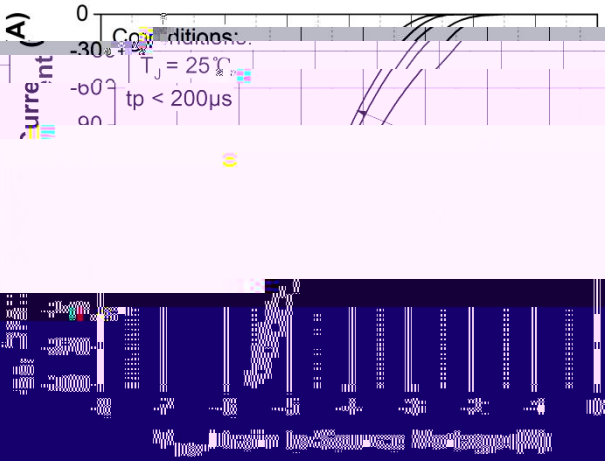
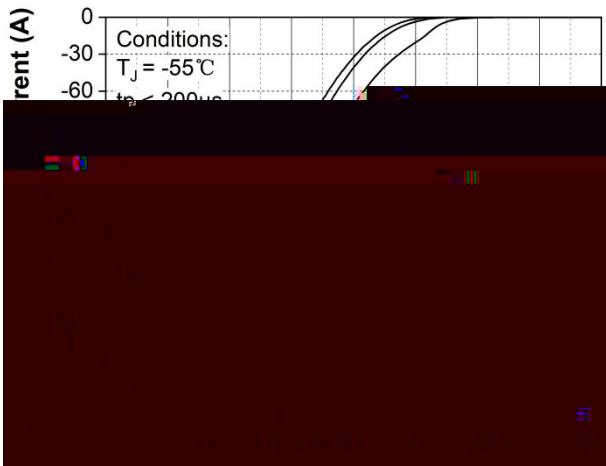
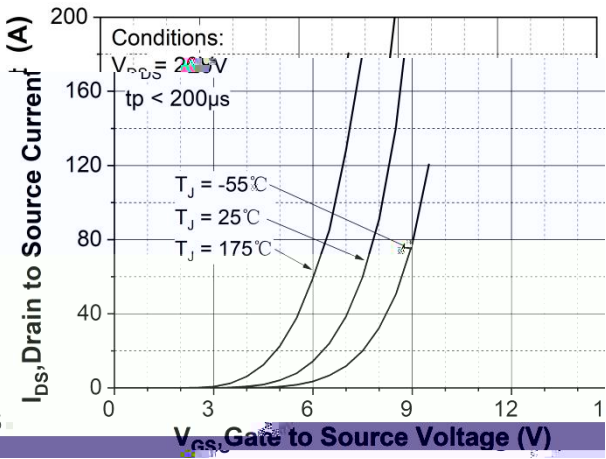


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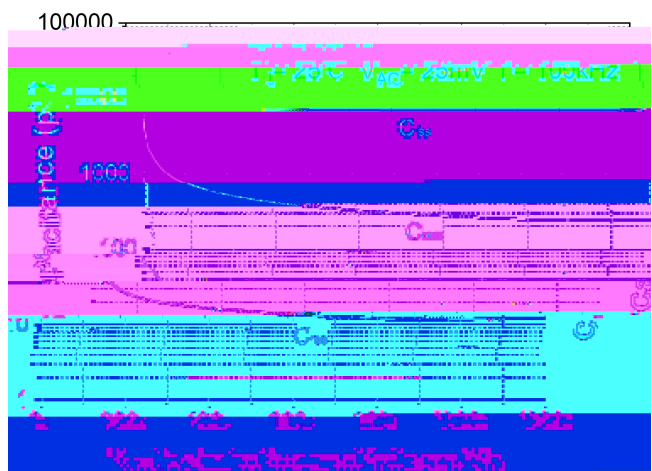
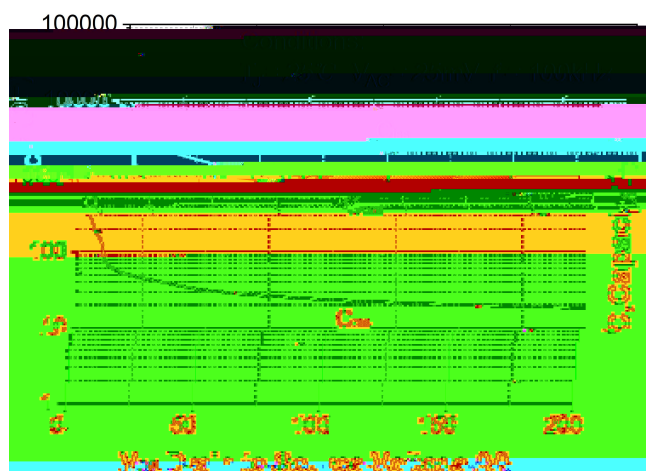
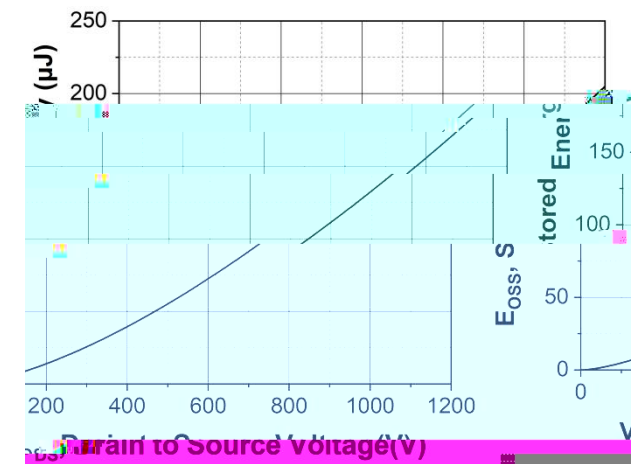
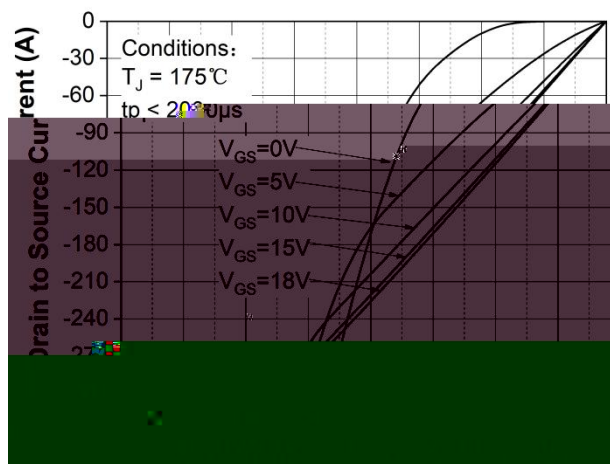
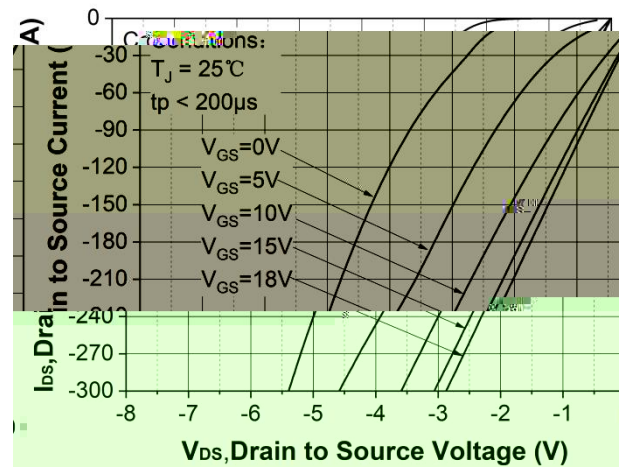
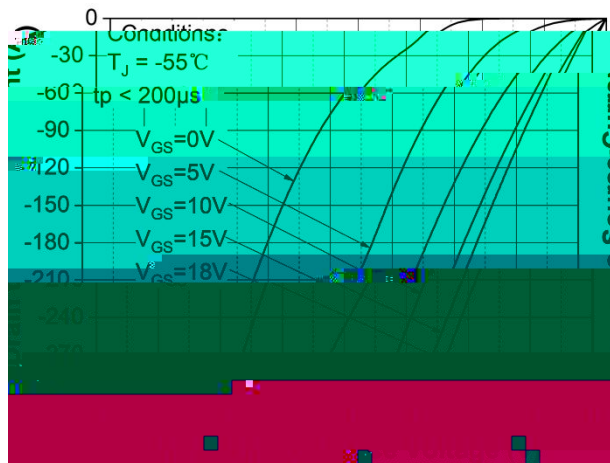
3 Electrical characteristic diagrams



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[illegible]

The diagram shows a rectangular layout with overall dimensions A (height) and B (width). The layout is divided into several regions:

- A top blue header region with height a_2 .
- A bottom yellow footer region with height a_3 .
- A central cyan region with height a_1 .
- Inside the cyan region, there is a small yellow square labeled G with width b_3 .
- To the right of G is a large gray rectangle labeled S with width b_1 .
- At the top left of the cyan region is a small gray square with width b_2 .
- Below the top gray square is another gray rectangle labeled S with width b_1 .

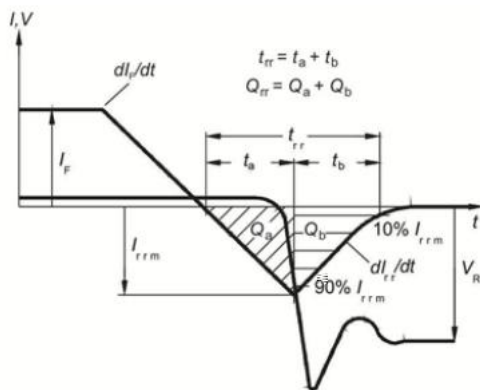
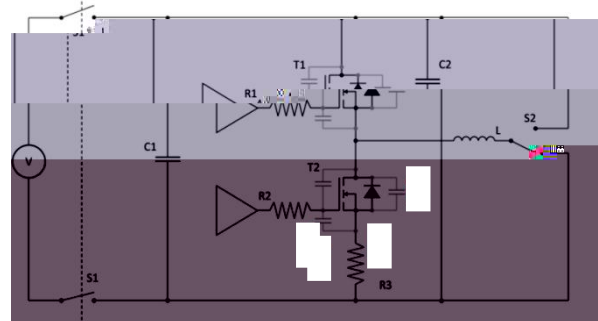
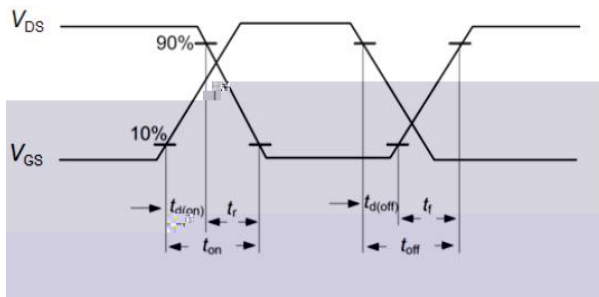
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5 Test conditions



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Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2026-06-26	Final	

Attention

RoHS compliance

REACH compliance

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